

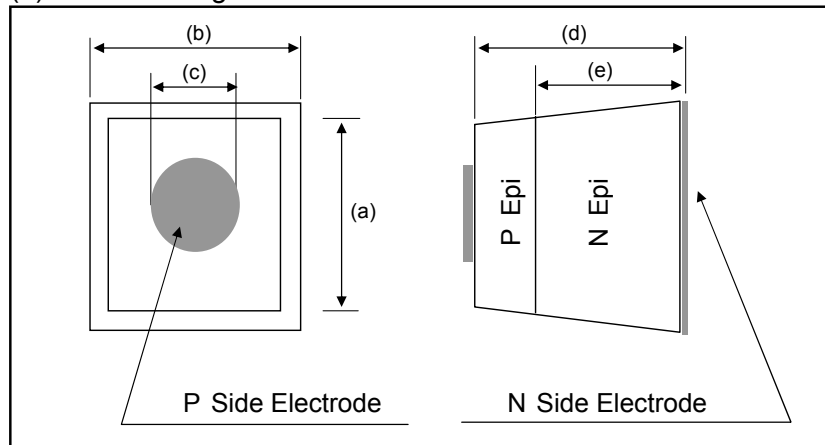
- 1. Material** Substrate GaAlAs (N Type) Removed
Epitaxial Layer GaAlAs (P/N Type)
- 2. Electrode** N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.1		V	IF=10uA
	$V_{F(2)}$		1.65	1.8	V	IF=50mA
Reverse Voltage	V_R	5			V	IR=10uA
Power	P_O	10	13		mW	IF=50mA
Wavelength	λ_P		850		nm	IF=50mA
	$\Delta\lambda$		45		nm	IF=50mA
Rise Time	Tr		25		ns	
Fall Time	Tf		13		ns	

※ Note : Power is measured by Sorter E/T system with bare chip.

- 4. Mechanical Data**
- | | | |
|---------------------|-------|-----------------|
| (a) Emission Area | ----- | 8.8mil x 8.8mil |
| (b) Bottom Area | ----- | 9.8mil x 9.8mil |
| (c) Bonding Pad | ----- | 130um |
| (d) Chip Thickness | ----- | 7.0mil |
| (e) Junction Height | ----- | 5.7mil |



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